

# Analysis of the transport process providing spin injection barrier

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Citation Report

#	ARTICLE	IF	CITATIONS
1	The electric field effect on spin injection in tunneling regime. Physics Letters, Section A: General, Atomic and Solid State Physics, 2003, 319, 367-372.	0.9	2
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7	Ballistic spin injection from Fe into ZnSe(001), (111), and (110), and into GaAs(001). Journal of Physics Condensed Matter, 2004, 16, 4643-4659.	0.7	17
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9	Electron Spin Dynamics in Semiconductors. Solid State Physics, 2004, 58, 73-166.	1.3	4
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17	High-field magnetoresistance of Fe/GaAs/Fe tunnel junctions. Journal of Applied Physics, 2004, 96, 2400-2402.	1.1	13
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